

Title (en)

PERFORATED SILICON MEMBRANE PROVIDED BY AN ELECTROCHEMICAL ETCHING METHOD

Title (de)

PERFORIERTE SILIZIUM-MEMBRAN, HERGESTELLT MITTELS EINES ELEKTROCHEMISCHEN ÄTZVERFAHRENS

Title (fr)

MEMBRANE EN SILICIUM PERFOREE PRODUITE SELON UN PROCEDE D'ATTAQUE ELECTROCHIMIQUE

Publication

**EP 1084285 A1 20010321 (DE)**

Application

**EP 99929077 A 19990503**

Priority

- DE 9901292 W 19990503
- DE 19820756 A 19980508

Abstract (en)

[origin: DE19820756C1] A perforated workpiece, comprising a silicon substrate (1) having a first region (6) with through-pores (4) and a second region (7) with blind pores, is new. An Independent claim is also included for producing a perforated workpiece by electrochemically etching one face (2) of a silicon substrate (1) to form pores (4) of depth less than the substrate thickness, providing the opposite substrate face (3) with a mask layer which exposes first regions (6) of this opposite substrate face, etching the exposed face regions (6) to the bottoms of the pores (4) and then removing the mask layer.

IPC 1-7

**C25F 3/12**

IPC 8 full level

**C25F 3/02** (2006.01); **C25F 3/12** (2006.01); **H01P 1/20** (2006.01)

CPC (source: EP KR US)

**C25F 3/02** (2013.01 - EP US); **C25F 3/12** (2013.01 - KR); **H01P 1/20** (2013.01 - EP US); **Y10T 428/24273** (2015.01 - EP US); **Y10T 428/24331** (2015.01 - EP US)

Citation (search report)

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